

# IMPORTANT NOTICE

10 December 2015

## 1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors

# DATA SHEET

## **BT152 series** Thyristors

Product specification

March 1997



## Thyristors

## BT152 series

## GENERAL DESCRIPTION

Glass passivated thyristors in a plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

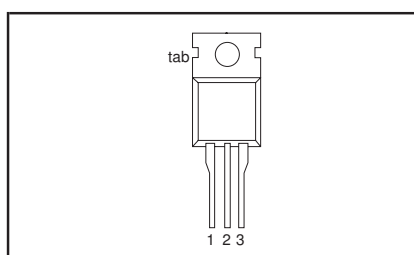
## QUICK REFERENCE DATA

| SYMBOL                   | PARAMETER                            | MAX.        | MAX.        | MAX.        | UNIT |
|--------------------------|--------------------------------------|-------------|-------------|-------------|------|
|                          | <b>BT152-</b>                        | <b>400R</b> | <b>600R</b> | <b>800R</b> |      |
| $V_{DRM}$ ,<br>$V_{RRM}$ | Repetitive peak off-state voltages   | 450         | 650         | 800         | V    |
| $I_{T(AV)}$              | Average on-state current             | 13          | 13          | 13          | A    |
| $I_{T(RMS)}$             | RMS on-state current                 | 20          | 20          | 20          | A    |
| $I_{TSM}$                | Non-repetitive peak on-state current | 200         | 200         | 200         | A    |

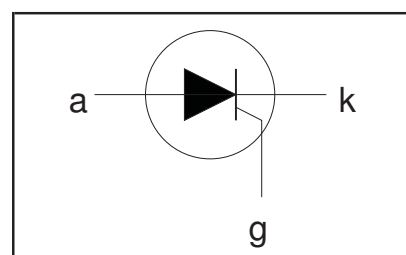
## PINNING - TO220AB

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | cathode     |
| 2   | anode       |
| 3   | gate        |
| tab | anode       |

## PIN CONFIGURATION



## SYMBOL



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

| SYMBOL       | PARAMETER                                                    | CONDITIONS                                                                              | MIN. | MAX.                             |                                  |                     | UNIT               |
|--------------|--------------------------------------------------------------|-----------------------------------------------------------------------------------------|------|----------------------------------|----------------------------------|---------------------|--------------------|
| $V_{DRM}$    | Repetitive peak off-state voltages                           |                                                                                         | -    | <b>-400R</b><br>450 <sup>1</sup> | <b>-600R</b><br>650 <sup>1</sup> | <b>-800R</b><br>800 | V                  |
| $I_{T(AV)}$  | Average on-state current                                     | half sine wave; $T_{mb} \leq 103\text{ }^{\circ}\text{C}$                               | -    | 13                               |                                  |                     | A                  |
| $I_{T(RMS)}$ | RMS on-state current                                         | all conduction angles                                                                   | -    | 20                               |                                  |                     | A                  |
| $I_{TSM}$    | Non-repetitive peak on-state current                         | half sine wave; $T_j = 25\text{ }^{\circ}\text{C}$ prior to surge                       | -    | 200                              |                                  |                     | A                  |
|              |                                                              | $t = 10\text{ ms}$                                                                      | -    | 220                              |                                  |                     | A                  |
| $I^2t$       | $I^2t$ for fusing                                            | $t = 8.3\text{ ms}$                                                                     | -    | 200                              |                                  |                     | A <sup>2</sup> s   |
| $dI_T/dt$    | Repetitive rate of rise of on-state current after triggering | $t = 10\text{ ms}$                                                                      | -    | 200                              |                                  |                     | A/ $\mu\text{s}$   |
|              |                                                              | $I_{TM} = 50\text{ A}$ ; $I_G = 0.2\text{ A}$ ;<br>$dI_G/dt = 0.2\text{ A}/\mu\text{s}$ | -    | 200                              |                                  |                     |                    |
| $I_{GM}$     | Peak gate current                                            |                                                                                         | -    | 5                                |                                  |                     | A                  |
| $V_{GM}$     | Peak gate voltage                                            |                                                                                         | -    | 5                                |                                  |                     | V                  |
| $V_{RGM}$    | Peak reverse gate voltage                                    |                                                                                         | -    | 5                                |                                  |                     | V                  |
| $P_{GM}$     | Peak gate power                                              |                                                                                         | -    | 20                               |                                  |                     | W                  |
| $P_{G(AV)}$  | Average gate power                                           | over any 20 ms period                                                                   | -    | 0.5                              |                                  |                     | W                  |
| $T_{stg}$    | Storage temperature                                          |                                                                                         | -40  | 150                              |                                  |                     | $^{\circ}\text{C}$ |
| $T_j$        | Operating junction temperature                               |                                                                                         | -    | 125                              |                                  |                     | $^{\circ}\text{C}$ |

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ $\mu\text{s}$ .

## Thyristors

## BT152 series

## THERMAL RESISTANCES

| SYMBOL         | PARAMETER                                       | CONDITIONS  | MIN. | TYP. | MAX. | UNIT |
|----------------|-------------------------------------------------|-------------|------|------|------|------|
| $R_{th\ j-mb}$ | Thermal resistance<br>junction to mounting base | in free air | -    | -    | 1.1  | K/W  |
| $R_{th\ j-a}$  | Thermal resistance<br>junction to ambient       |             | -    | 60   | -    | K/W  |

## STATIC CHARACTERISTICS

 $T_j = 25\text{ °C}$  unless otherwise stated

| SYMBOL     | PARAMETER                 | CONDITIONS                                                    | MIN. | TYP. | MAX. | UNIT |
|------------|---------------------------|---------------------------------------------------------------|------|------|------|------|
| $I_{GT}$   | Gate trigger current      | $V_D = 12\text{ V}; I_T = 0.1\text{ A}$                       | -    | 3    | 32   | mA   |
| $I_L$      | Latching current          | $V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$                    | -    | 25   | 80   | mA   |
| $I_H$      | Holding current           | $V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$                    | -    | 15   | 60   | mA   |
| $V_T$      | On-state voltage          | $I_T = 40\text{ A}$                                           | -    | 1.4  | 1.75 | V    |
| $V_{GT}$   | Gate trigger voltage      | $V_D = 12\text{ V}; I_T = 0.1\text{ A}$                       | -    | 0.6  | 1.5  | V    |
| $I_D, I_R$ | Off-state leakage current | $V_D = V_{DRM(max)}; I_T = 0.1\text{ A}; T_j = 125\text{ °C}$ | 0.25 | 0.4  | -    | V    |
|            |                           | $V_D = V_{DRM(max)}; V_R = V_{RRM(max)}; T_j = 125\text{ °C}$ | -    | 0.2  | 1.0  | mA   |

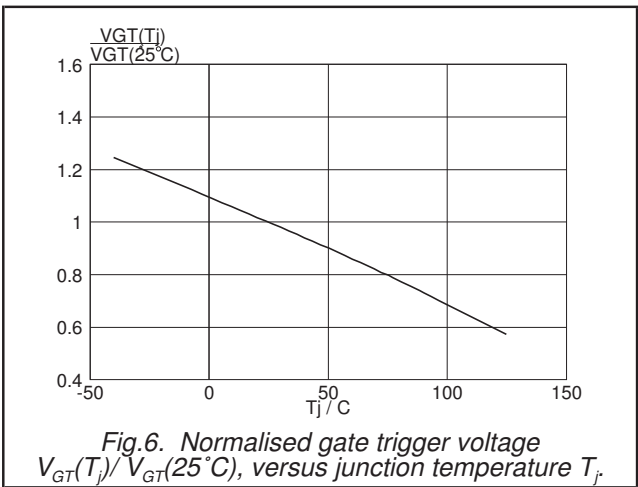
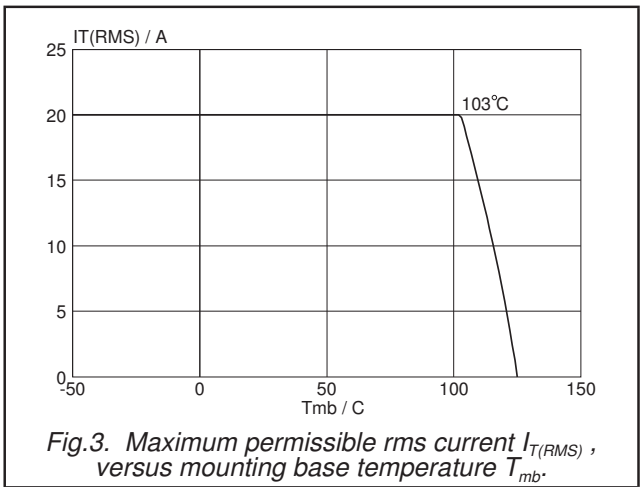
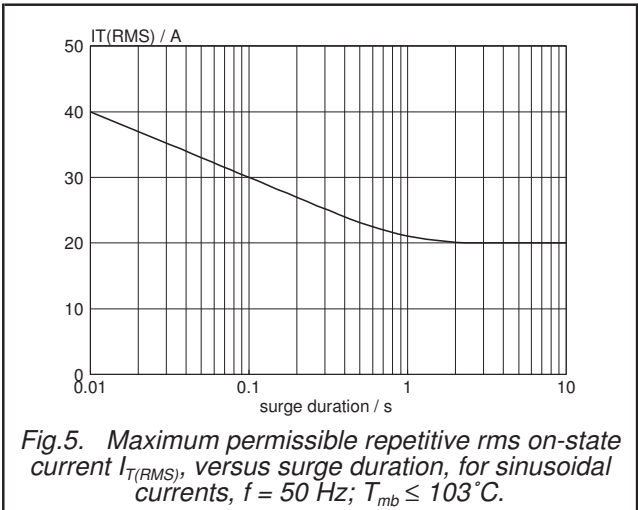
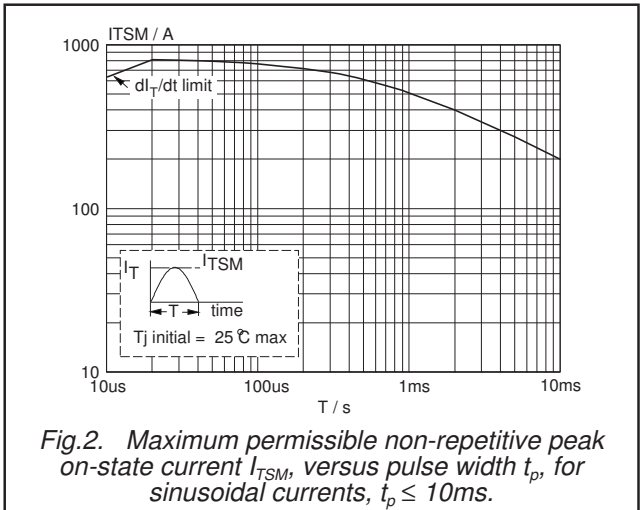
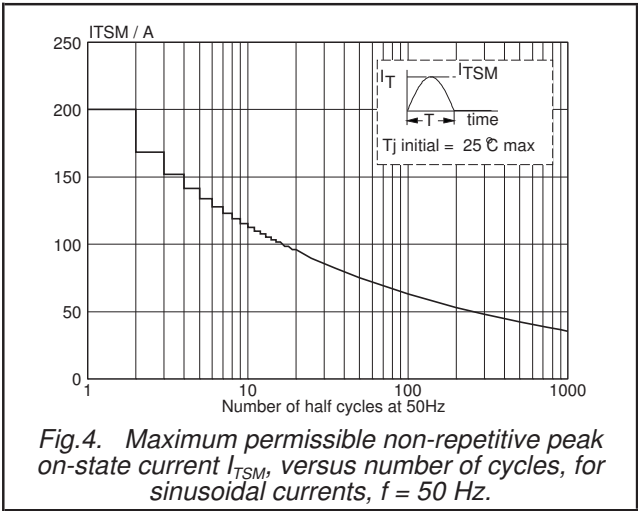
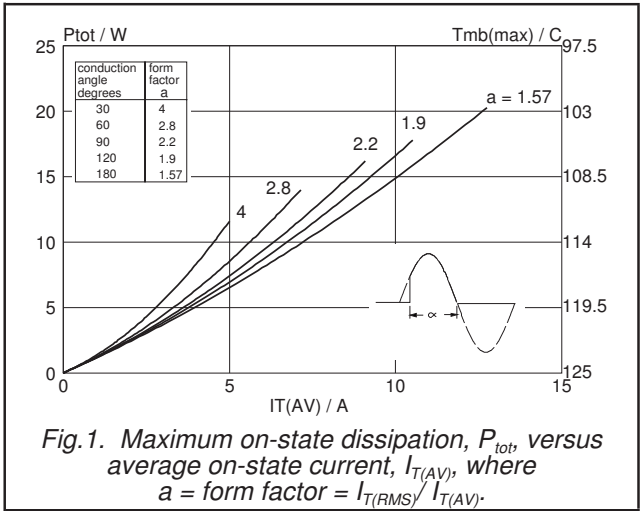
## DYNAMIC CHARACTERISTICS

 $T_j = 25\text{ °C}$  unless otherwise stated

| SYMBOL    | PARAMETER                                     | CONDITIONS                                                                                                                                                                                       | MIN. | TYP. | MAX. | UNIT       |
|-----------|-----------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|------|------|------------|
| $dV_D/dt$ | Critical rate of rise of<br>off-state voltage | $V_{DM} = 67\% V_{DRM(max)}; T_j = 125\text{ °C};$<br>exponential waveform gate open circuit                                                                                                     | 200  | 300  | -    | V/ $\mu$ s |
| $t_{gt}$  | Gate controlled turn-on<br>time               | $V_D = V_{DRM(max)}; I_G = 0.1\text{ A}; dI_G/dt = 5\text{ A}/\mu\text{s};$<br>$I_{TM} = 40\text{ A}$                                                                                            | -    | 2    | -    | $\mu$ s    |
| $t_q$     | Circuit commutated<br>turn-off time           | $V_D = 67\% V_{DRM(max)}; T_j = 125\text{ °C};$<br>$I_{TM} = 50\text{ A}; V_R = 25\text{ V}; dI_{TM}/dt = 30\text{ A}/\mu\text{s};$<br>$dV_D/dt = 50\text{ V}/\mu\text{s}; R_{GK} = 100\ \Omega$ | -    | 70   | -    | $\mu$ s    |

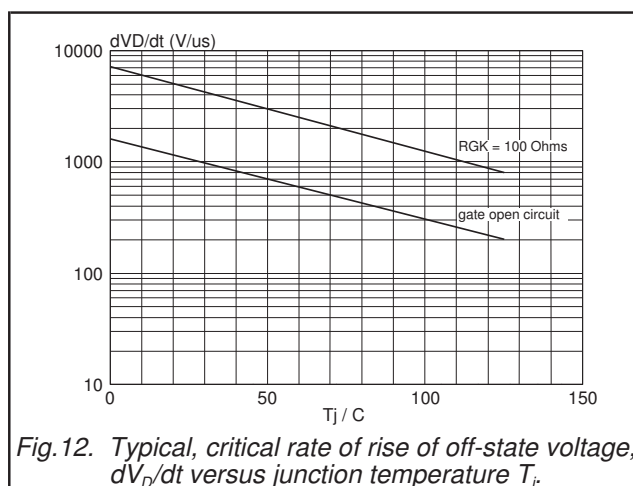
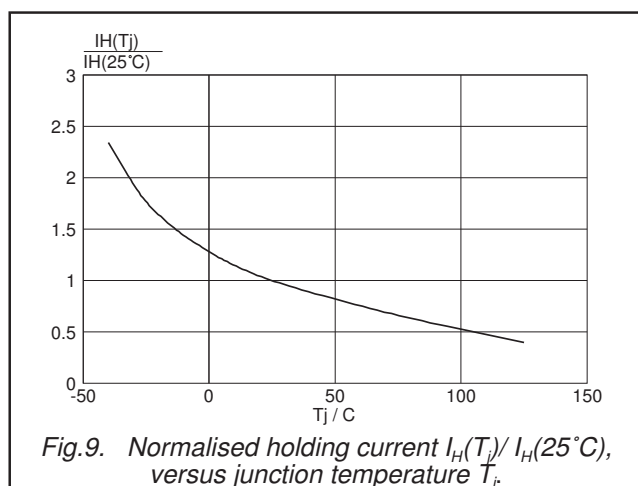
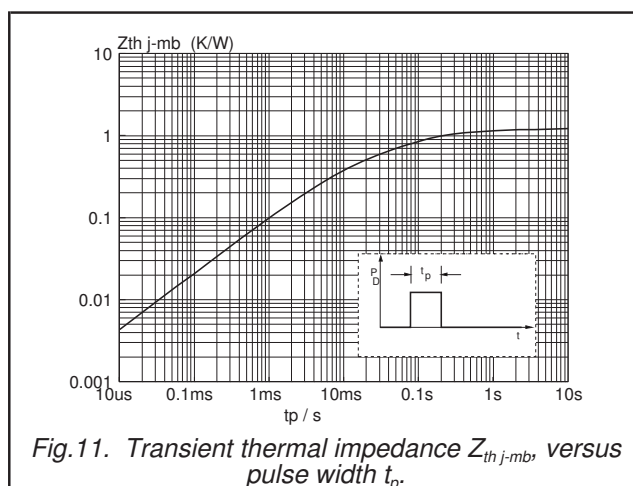
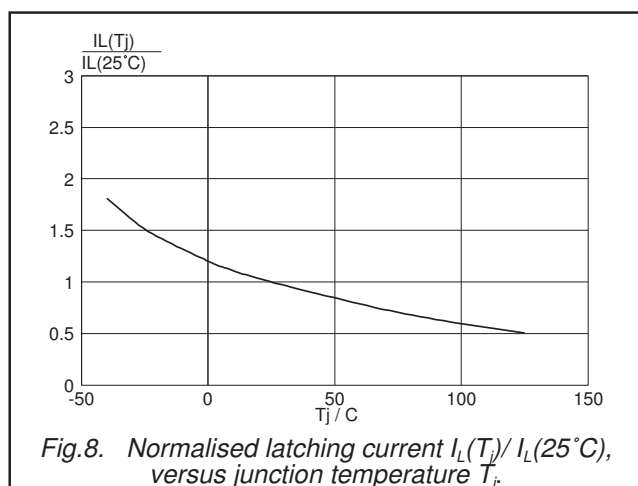
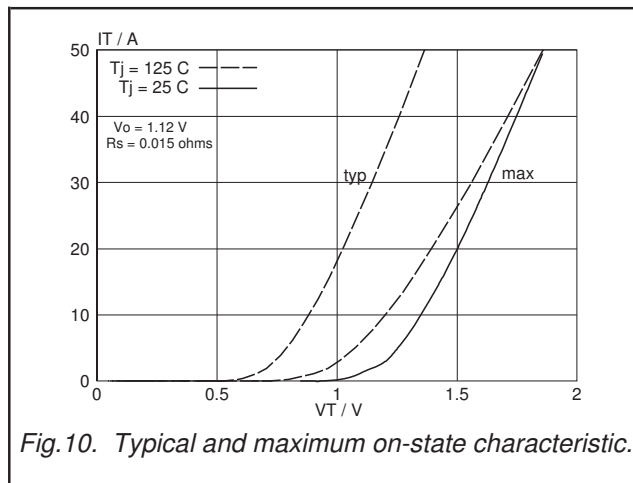
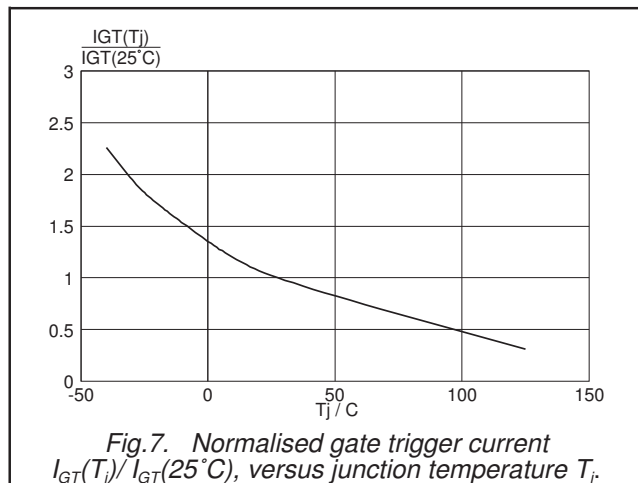
Thyristors

BT152 series



## Thyristors

## BT152 series



## Thyristors

## BT152 series

## MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

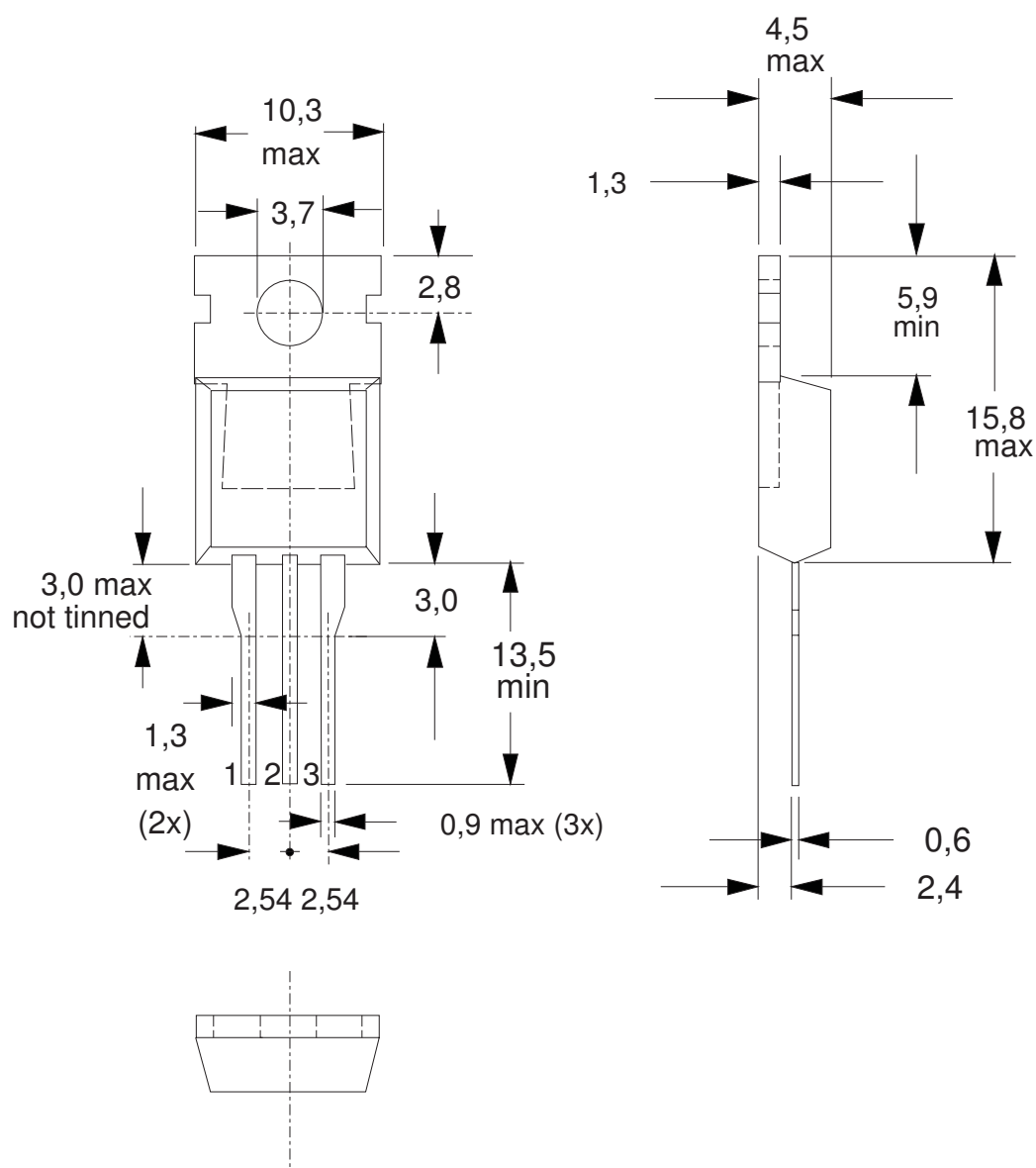


Fig.13. TO220AB; pin 2 connected to mounting base.

## Notes

1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

## Legal information

### DATA SHEET STATUS

| DOCUMENT STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITION                                                                            |
|--------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective data sheet           | Development                   | This document contains data from the objective specification for product development. |
| Preliminary data sheet         | Qualification                 | This document contains data from the preliminary specification.                       |
| Product data sheet             | Production                    | This document contains the product specification.                                     |

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